

74HC175; 74HCT175

Quad D-type flip-flop with reset; positive-edge trigger

Rev. 5 — 29 January 2016

Product data sheet

1. General description

The 74HC175; 74HCT175 is a quad positive-edge triggered D-type flip-flop with individual data inputs (D_n) and complementary outputs (Q_n and $\overline{Q_n}$). The common clock (CP) and master reset ($\overline{MR}$) inputs load and reset all flip-flops simultaneously. The D-input that meets the set-up and hold time requirements on the LOW-to-HIGH clock transition will be stored in the flip-flop and appear at the Q output. A LOW on $\overline{MR}$ causes the flip-flops and outputs to be reset LOW. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

2. Features and benefits

- Input levels:
 - ◆ For 74HC175: CMOS level
 - ◆ For 74HCT175: TTL level
- Four edge-triggered D-type flip-flops
- Asynchronous master reset
- Complies with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V.
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$.

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC175D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT175D				
74HC175DB	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT175DB				
74HC175PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT175PW				



4. Functional diagram

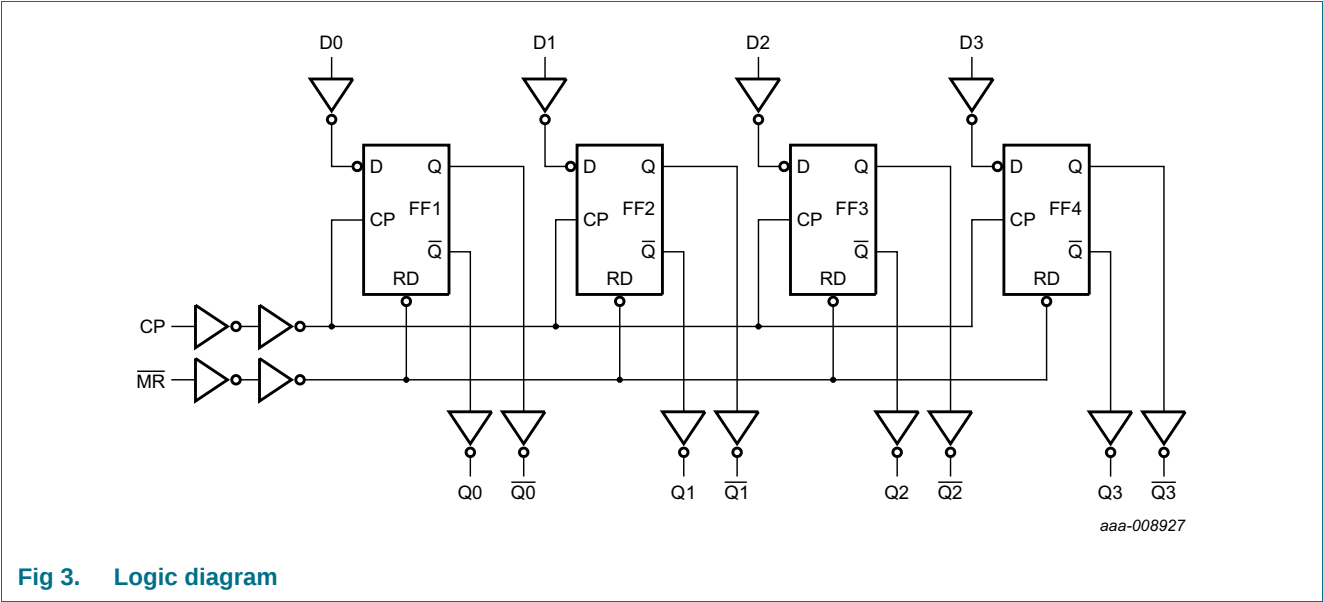
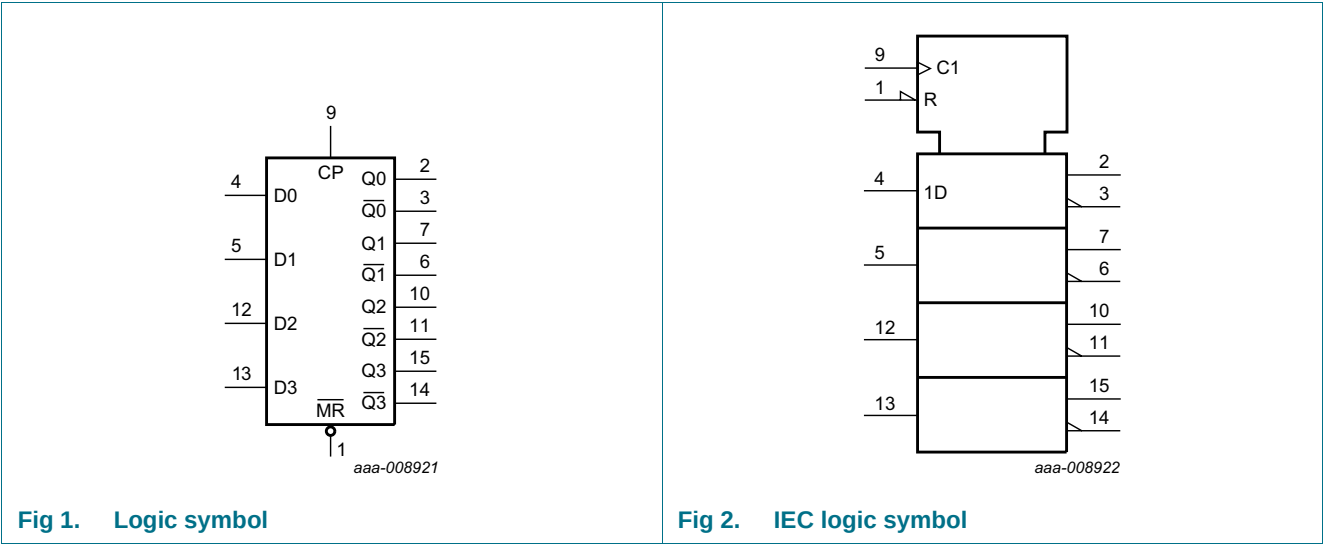


Fig 3. Logic diagram

5. Pinning information

5.1 Pinning

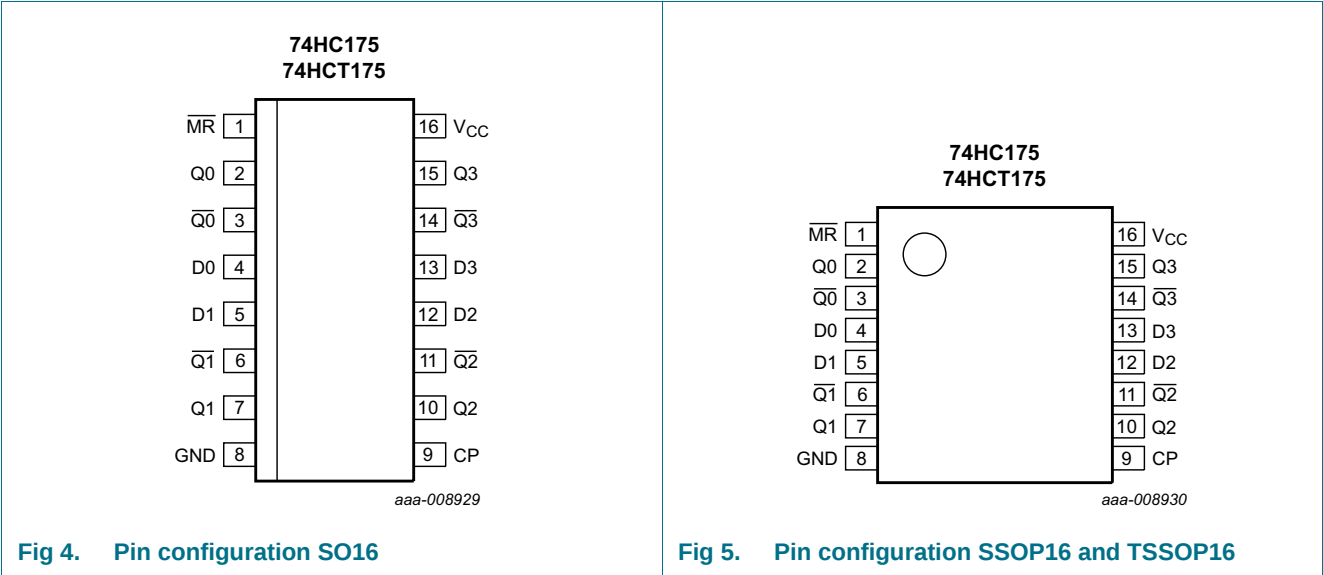


Fig 4. Pin configuration SO16

Fig 5. Pin configuration SSOP16 and TSSOP16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
MR	1	asynchronous master reset input (active LOW)
Q0 to Q3	2, 7, 10, 15	flip-flop output
Q0̄ to Q3̄	3, 6, 11, 14	complementary flip-flop output
D0 to D3	4, 5, 12, 13	data input
GND	8	ground (0 V)
CP	9	clock input (LOW-to-HIGH edge-triggered)
VCC	16	positive supply voltage

6. Functional description

Table 3. Function table^[1]

Operating modes	Inputs			Outputs	
	MR	CP	Dn	Qn	$\overline{Qn}$
reset (clear)	L	X	X	L	H
load "1"	H	↑	h	H	L
load "0"	H	↑	l	L	H

- [1] H = HIGH voltage level;
h = HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition;
L = LOW voltage level;
l = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition;
X = don't care;
↑ = LOW-to-HIGH clock transition.

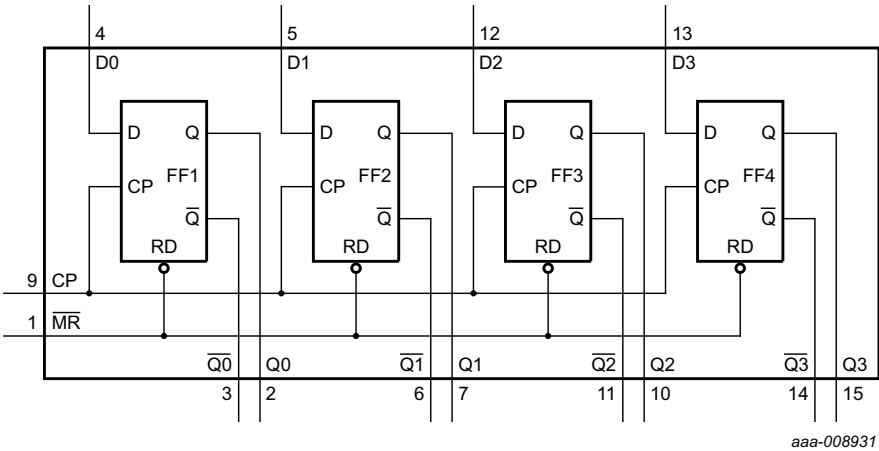


Fig 6. Functional diagram

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_O	output current	$-0.5\text{ V} < V_O < V_{CC} + 0.5\text{ V}$	-	± 25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$			
		SO16, SSOP16 and TSSOP16 [1]	-	500	mW

[1] For SO16 package: above 70 °C the value of P_{tot} derates linearly with 8 mW/K.

For SSOP16 and TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC175			74HCT175			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit		
			Min	Typ	Max	Min	Max	Min	Max			
74HC175												
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V		
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V		
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V		
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V		
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V		
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V		
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}										
		I _O = –20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V		
		I _O = –20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V		
		I _O = –20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V		
		I _O = –4.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V		
V _{OL}	LOW-level output voltage	I _O = –5.2 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V		
		V _I = V _{IH} or V _{IL}										
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V		
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V		
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V		
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1	-	±1	μA		
		I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA
		C _I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT175												
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V		
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V		
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V										
		I _O = –20 μA	4.4	4.5	-	4.4	-	4.4	-	V		
		I _O = –4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V		
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V										
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V		
		I _O = 5.2 mA; V _{CC} = 5.5 V	-	0.15	0.26	-	0.33	-	0.4	V		
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1	-	±1	μA		

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	8.0	-	80	-	160	μA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} – 2.1 V; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V								
		Dn input	-	40	144	-	180	-	196	μA
		CP input	-	60	216	-	270	-	294	μA
		MR input	-	100	360	-	450	-	490	μA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristicsGND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit, see [Figure 10](#)

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC175										
t _{pd}	propagation delay	CP to Qn, $\overline{Qn}$; see Figure 7 [1]								
		V _{CC} = 2.0 V	-	55	175	-	220	-	265	ns
		V _{CC} = 4.5 V	-	20	35	-	44	-	53	ns
		V _{CC} = 5 V; C _L = 15 pF	-	17	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	16	30	-	37	-	45	ns
t _{PHL}	HIGH to LOW propagation delay	$\overline{MR}$ to Qn, $\overline{Qn}$; see Figure 9								
		V _{CC} = 2.0 V	-	50	150	-	190	-	225	ns
		V _{CC} = 4.5 V	-	18	30	-	38	-	45	ns
		V _{CC} = 5 V; C _L = 15 pF	-	15	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	14	26	-	33	-	38	ns
t _t	transition time	Qn output; see Figure 7 [2]								
		V _{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V _{CC} = 6.0 V	-	6	13	-	16	-	19	ns

Table 7. Dynamic characteristics ...continuedGND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see [Figure 10](#)

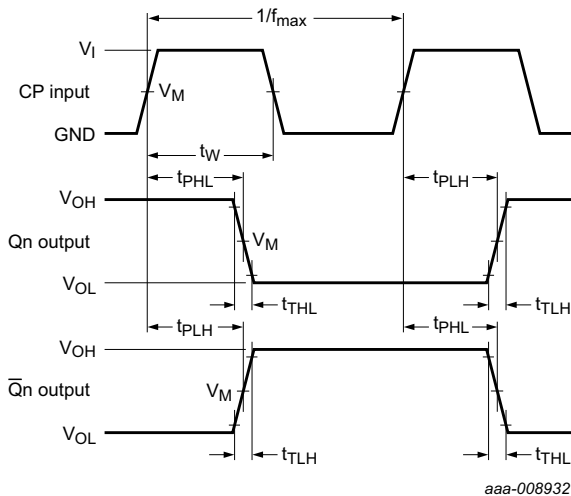
Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_W	pulse width	CP input HIGH or LOW; see Figure 7								
		$V_{CC} = 2.0$ V	80	22	-	100	-	120	-	ns
		$V_{CC} = 4.5$ V	16	8	-	20	-	24	-	ns
		$V_{CC} = 6.0$ V	14	6	-	17	-	20	-	ns
		$\overline{MR}$ input LOW; see Figure 9								
		$V_{CC} = 2.0$ V	80	19	-	100	-	120	-	ns
		$V_{CC} = 4.5$ V	16	7	-	20	-	24	-	ns
		$V_{CC} = 6.0$ V	14	6	-	17	-	20	-	ns
t_{rec}	recovery time	$\overline{MR}$ to CP; see Figure 9								
		$V_{CC} = 2.0$ V	5	–33	-	5	-	5	-	ns
		$V_{CC} = 4.5$ V	5	–12	-	5	-	5	-	ns
		$V_{CC} = 6.0$ V	5	–10	-	5	-	5	-	ns
t_{su}	set-up time	Dn to CP; see Figure 7								
		$V_{CC} = 2.0$ V	80	3	-	100	-	120	-	ns
		$V_{CC} = 4.5$ V	16	1	-	20	-	24	-	ns
		$V_{CC} = 6.0$ V	14	1	-	17	-	20	-	ns
t_h	hold time	Dn to CP; see Figure 7								
		$V_{CC} = 2.0$ V	25	2	-	30	-	40	-	ns
		$V_{CC} = 4.5$ V	5	0	-	6	-	8	-	ns
		$V_{CC} = 6.0$ V	4	0	-	5	-	7	-	ns
f_{max}	maximum frequency	CP input; see Figure 7								
		$V_{CC} = 2.0$ V	6	25	-	4.8	-	4	-	MHz
		$V_{CC} = 4.5$ V	30	75	-	24	-	20	-	MHz
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	83	-	-	-	-	-	MHz
		$V_{CC} = 6.0$ V	35	89	-	28	-	24	-	MHz
C_{PD}	power dissipation capacitance	per package; $V_I = \text{GND to } V_{CC}$ [3]	-	32	-	-	-	-	-	pF

Table 7. Dynamic characteristics ...continuedGND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see [Figure 10](#)

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT175										
t _{pd}	propagation delay	CP to Qn, $\overline{Qn}$; see Figure 7 ^[1]								
		V _{CC} = 4.5 V	-	19	33	-	41	-	50	ns
		V _{CC} = 5 V; C _L = 15 pF	-	16	-	-	-	-	-	ns
t _{PHL}	HIGH to LOW propagation delay	MR to Qn; see Figure 9								
		V _{CC} = 4.5 V	-	22	38	-	48	-	57	ns
		V _{CC} = 5 V; C _L = 15 pF	-	19	-	-	-	-	-	ns
		$\overline{MR}$ to $\overline{Qn}$; see Figure 9								
		V _{CC} = 4.5 V	-	19	35	-	44	-	53	ns
		V _{CC} = 5 V; C _L = 15 pF	-	16	-	-	-	-	-	ns
t _t	transition time	Qn output; see Figure 7 ^[2]								
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
t _W	pulse width	CP input; see Figure 7								
		V _{CC} = 4.5 V	20	12	-	25	-	30	-	ns
		$\overline{MR}$ input LOW; see Figure 9								
		V _{CC} = 4.5 V	20	11	-	25	-	30	-	ns
t _{rec}	recovery time	$\overline{MR}$ to CP; see Figure 9								
		V _{CC} = 4.5 V	5	–10	-	5	-	5	-	ns
t _{su}	set-up time	Dn to CP; see Figure 7								
		V _{CC} = 4.5 V	16	5	-	20	-	24	-	ns
t _h	hold time	Dn to CP; see Figure 7								
		V _{CC} = 4.5 V	5	0	-	5	-	5	-	ns
f _{max}	maximum frequency	CP input; see Figure 7								
		V _{CC} = 4.5 V	25	49	-	20	-	17	-	MHz
		V _{CC} = 5 V; C _L = 15 pF	-	54	-	-	-	-	-	MHz
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V ^[3]	-	34	-	-	-	-	-	pF

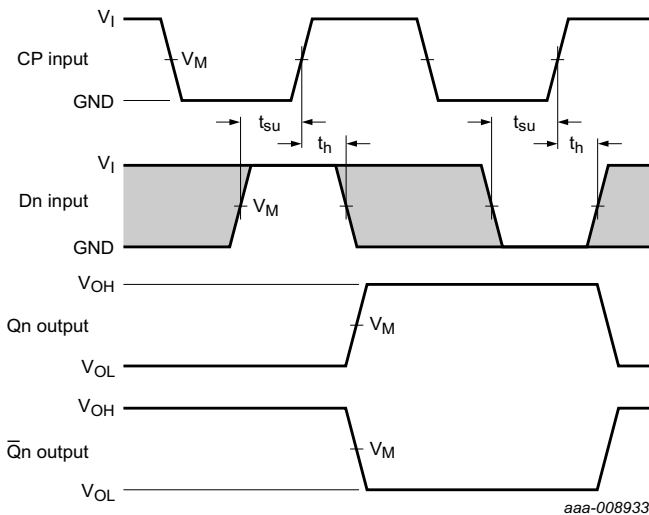
[1] t_{pd} is the same as t_{PHL} and t_{PLH} .[2] t_t is the same as t_{THL} and t_{TLH} .[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW). $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where: f_i = input frequency in MHz; f_o = output frequency in MHz; $\Sigma (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs; C_L = output load capacitance in pF; V_{CC} = supply voltage in V.

11. Waveforms



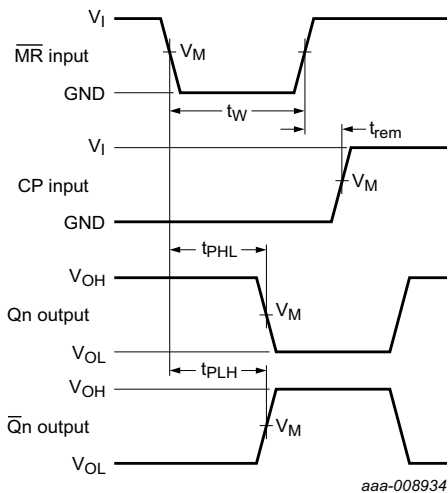
Measurement points are given in [Table 8](#).

Fig 7. Input to output propagation delay, output transition time, clock input pulse width and maximum frequency



Measurement points are given in [Table 8](#).

Fig 8. Data set-up and hold times for data input

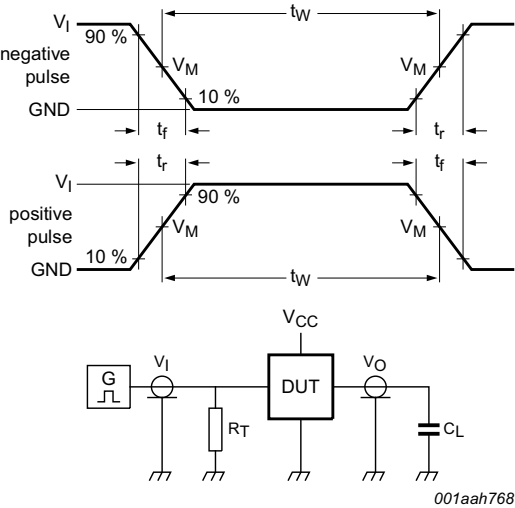


Measurement points are given in [Table 8](#).

Fig 9. Master reset to output propagation delays, master reset pulse width and master reset to clock recovery time

Table 8. Measurement points

Type	Input		Output
	V_I	V_M	V_M
74HC175	V_{CC}	$0.5V_{CC}$	$0.5V_{CC}$
74HCT175	3 V	1.3 V	1.3 V



Test data is given in [Table 9](#).
Definitions for test circuit:
 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.
 C_L = Load capacitance including jig and probe capacitance.
 R_L = Load resistance.

Fig 10. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load		Test
	V_I	t_r, t_f	C_L	R_L	
74HC175	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	t_{PLH}, t_{PHL}
74HCT175	3 V	6 ns	15 pF, 50 pF	1 k Ω	t_{PLH}, t_{PHL}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

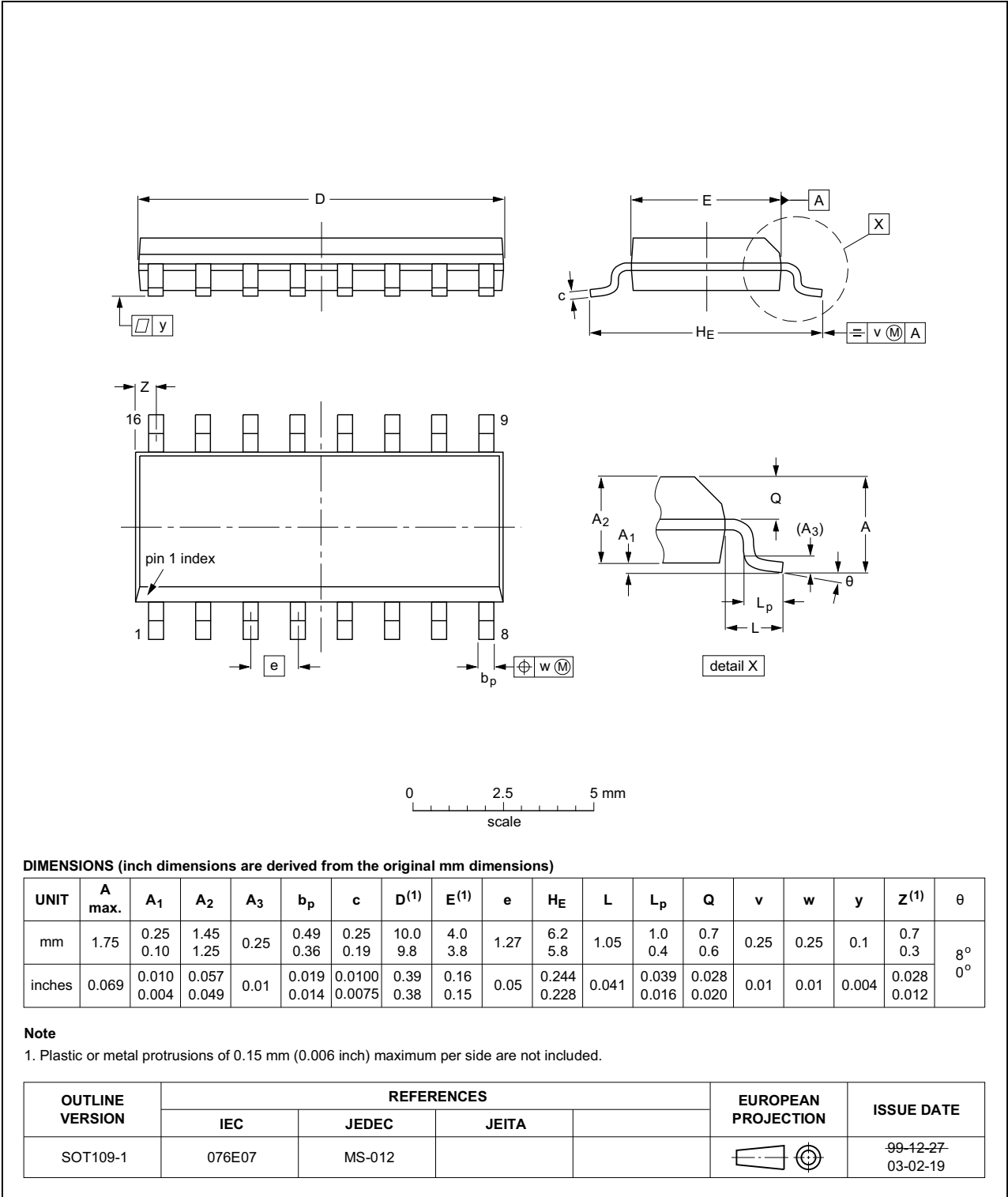


Fig 11. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

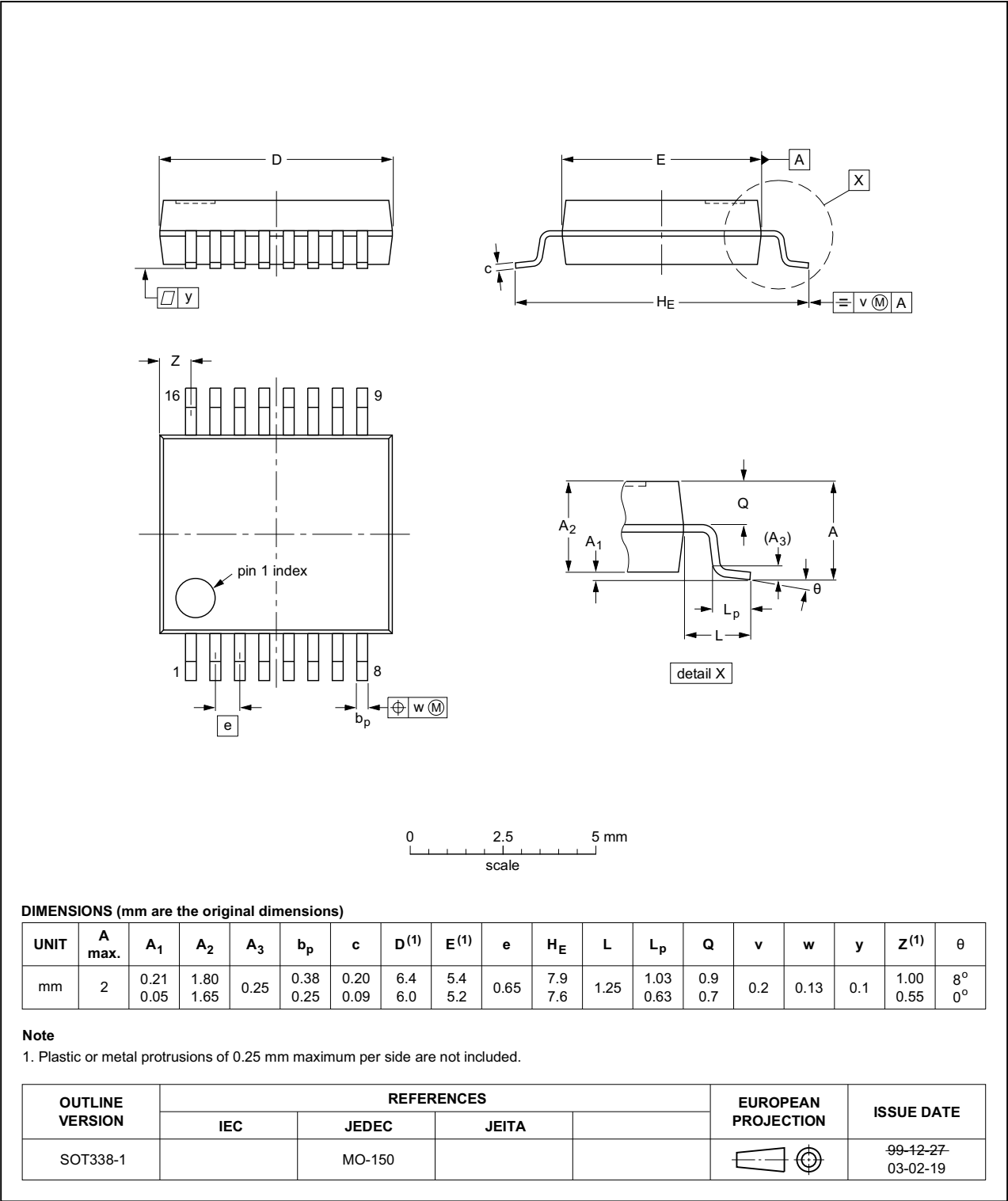


Fig 12. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

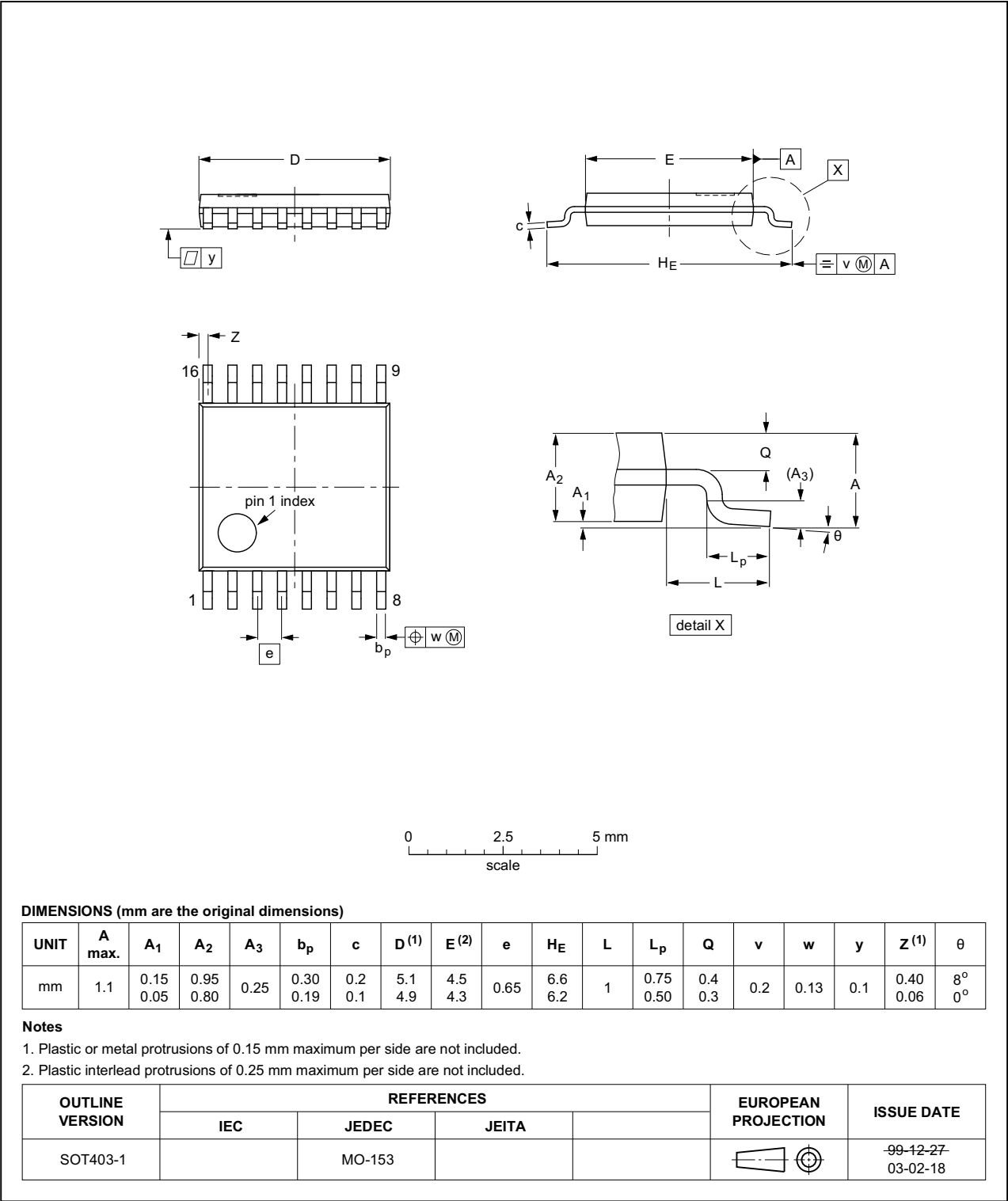


Fig 13. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT175 v.5	20160129	Product data sheet	-	74HC_HCT175 v.4
Modifications:	• Type numbers 74HC175N and 74HCT175N (SOT38-4) removed.			
74HC_HCT175 v.4	20140408	Product data sheet	-	74HC_HCT175 v.3
Modifications:	• General description corrected (errata).			
74HC_HCT175 v.3	20140331	Product data sheet	-	74HC_HCT175_CNV_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate.			
74HC_HCT175_CNV_2	19980708	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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